

General Description

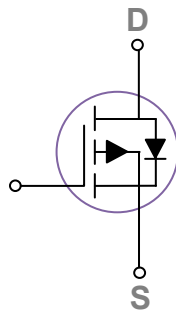
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
-30V	3.3mΩ	-100A

Features

- -30V,-100A, $R_{DS(ON)} = 3.3m\Omega @ V_{GS} = -10V$
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

PPAK5X6 Pin Configuration



Applications

- Motor Driver Applications
- POL Applications
- Load Switch
- LED Application

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	-100	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	-63.2	A
I_{DM}	Drain Current – Pulsed ¹	-400	A
EAS	Single Pulse Avalanche Energy (Note 2)	320	mJ
IAS	Single Pulse Avalanche Current (Note 2)	80	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	138	W
	Power Dissipation – Derate above 25°C	1.11	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.9	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-30A$	---	2.6	3.3	$m\Omega$
		$V_{GS}=-4.5V, I_D=-20A$	---	3.8	5	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.6	-2.2	V
gfs	Forward Transconductance	$V_{DS}=-10V, I_D=-3A$	---	20	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{3,4}	$V_{DS}=-24V, V_{GS}=-10V, I_D=-10A$	---	146	210	nC
Q_{gs}	Gate-Source Charge ^{3,4}		---	22	44	
Q_{gd}	Gate-Drain Charge ^{3,4}		---	32	64	
$T_{d(on)}$	Turn-On Delay Time ^{3,4}	$V_{DD}=-15V, V_{GS}=-10V, R_G=5\Omega, I_D=-10A$	---	17	34	ns
T_r	Rise Time ^{3,4}		---	61	120	
$T_{d(off)}$	Turn-Off Delay Time ^{3,4}		---	200	400	
T_f	Fall Time ^{3,4}		---	113	220	
C_{iss}	Input Capacitance	$V_{DS}=-25V, V_{GS}=0V, F=1\text{MHz}$	---	7930	12000	pF
C_{oss}	Output Capacitance		---	983	1300	
C_{rss}	Reverse Transfer Capacitance		---	505	750	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V, \text{Force Current}$	---	---	-100	A
I_{SM}	Pulsed Source Current		---	---	-200	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$V_{GS}=0V, I_S=-20A,$	---	52	---	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	53	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=80A, R_G=25\Omega$. Starting $T_J=25^\circ\text{C}$.
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

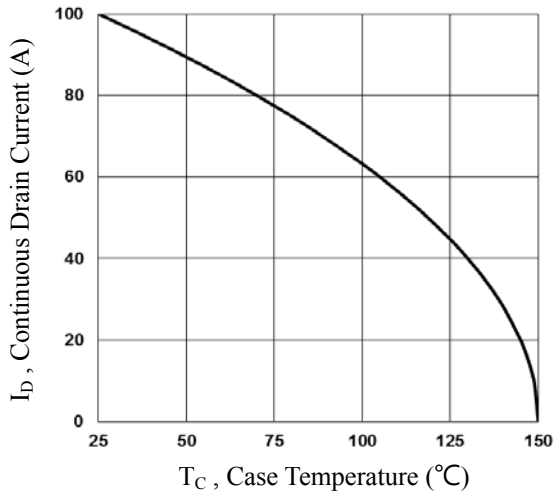


Fig.1 Continuous Drain Current vs. T_c

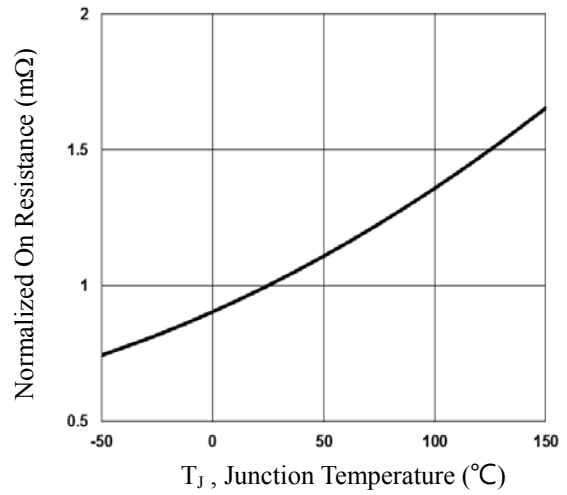


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

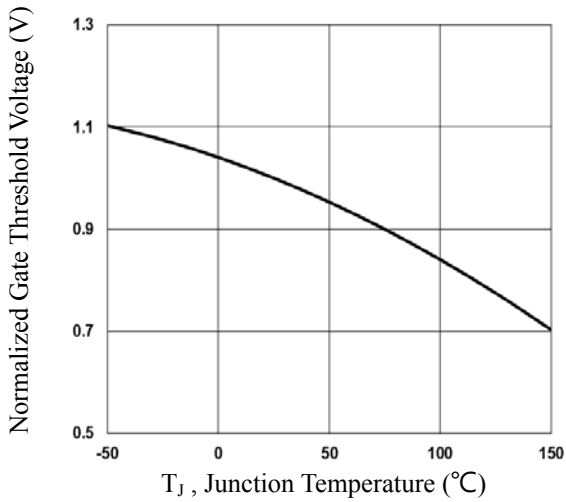


Fig.3 Normalized V_{th} vs. T_j

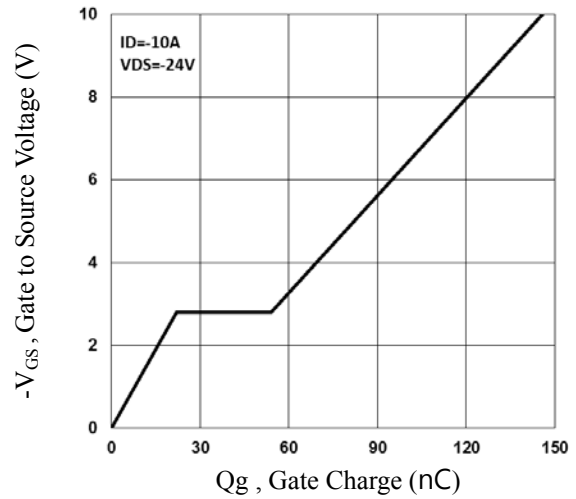


Fig.4 Gate Charge Waveform

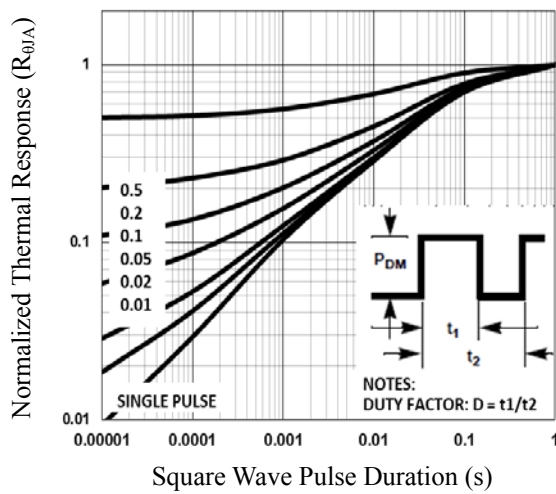


Fig.5 Normalized Transient Impedance

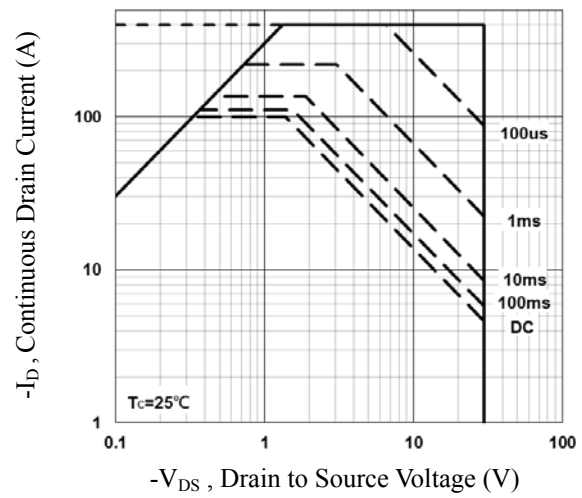


Fig.6 Maximum Safe Operation Area